

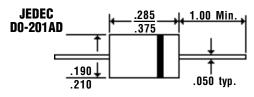
Preliminary Data Sheet | 3.0 Amp Glass Passivated **Sintered Ultra - Fast Rectifiers**

UGPZ30A...30G Series

Semiconductor Description



Mechanical Dimensions



Features

- LOWEST COST FOR GLASS SINTERED **ULTRA - FAST CONSTRUCTION**
- LOWEST V. FOR GLASS SINTERED **ULTRA - FAST CONSTRUCTION**
- TYPICAL I_R < 100 nAmps

- 3.0 AMP OPERATION @ T_A = 55°C, WITH **NO THERMAL RUNAWAY**
- SINTERED GLASS CAVITY-FREE JUNCTION

Electrical Characteristics @ 25°C. Maximum Ratings	UGPZ30A 30G Series				Units
	30A	30B	30D	30G	
Peak Repetitive Reverse VoltageV _{RRM}	50	100	200	400	Volts
RMS Reverse Voltage $V_{R(rms)}$	35	70	140	280	Volts
DC Blocking VoltageV _{DC}	50	100	200	400	Volts
Average Forward Rectified CurrentI _{F(av)} Current 3/8" Lead Length @ T _A = 55°C	3.0			Amps	
Non-Repetitive Peak Forward Surge CurrentI _{FSM} 8.3mS, ½ Sine Wave Superimposed on Rated Load	125				Amps
Forward Voltage @ Rated Forward Current and 25°CV _F	<> 1.2			> 1.25	Volts
Full Load Reverse CurrentI _R (av) Full Cycle Average @ T _A = 55°C	100				μAmps
DC Reverse CurrentI $_{R(max)}$ @ Rated DC Blocking Voltage $T_A = 25^{\circ}C$ $T_A = 150^{\circ}C$		5 2			μAmp μAmp
Typical Junction CapacitanceC _J (Note 1)		6	0		рF
Maximum Thermal ResistanceR _{eJA} (Note 2)		1	6		°C/W
Maximum Reverse Recovery Timet _{RR} (Note 3)		3	35		nS
Operating & Storage Temperature RangeT,, T _{STRG}		65 t	o 175		°C

NOTES: 1. Measured @ 1 MHZ and applied reverse voltage of 4.0V.

- 2. Thermal Resistance from Junction to Ambient at 3/8" Lead Length, P.C. Board Mounted.
- 3. Reverse Recovery Condition $I_F = 0.5A$, $I_R = 1.0A$, $I_{RR} = 0.25A$.